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TO	Examiner Ginette Peralta	August 12, 2004
	NAME	DATE
	USPTO	703-872-9306
	COMPANY/FIRM	FAX #
	NUMBER OF PAGES INCLUDING COVER: 2	CONFIRM FAX: <input checked="" type="checkbox"/> YES <input type="checkbox"/> NO
FROM	Choongsoo Park	218207US-2 PCT
	NAME	OUR REFERENCE
	703-412-4533	10/030,175
	DIRECT PHONE #	YOUR REFERENCE

## MESSAGE

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Re: Application No. 10/030,175  
To: Examiner Peralta  
From: Choongsoo Park

Per our discussion this morning, I will give you a call around 2:00 p.m. Please find below our client's comments on the outstanding rejections.

Comments:

Claim 1

Boyd does not show the step of selectively siliciding the source and the drain from a metal layer covering said source and drain.

This step is shown in Misra (see figure 13 and col. 9, lines 45-53).

Boyd does not disclose the step of depositing at least one contact metal layer on the drain, source and dummy gate and the step of polishing said metal layer with stop on the dummy gate. The layer 60 deposited on the drain, source and dummy gate is a dielectric layer.

Misra does not disclose the step of depositing said contact metal layer and the polishing step with stop on the dummy gate.

A first dielectric layer 120 (nitride) and a second dielectric layer 122 are deposited on drain, source and dummy gate. The polishing stops at the dummy gate.

Ismail discloses a method for fabricating an electric component wherein a contact metal layer 15 is directly deposited on the shallow junction regions 4.

Ismail mentions column 1, line 66 to column 2, line 2 that no silicidation step is needed.

Consequently, there would be no motivation to substitute the dielectric layer 60 of Boyd or the dielectric layers 120, 122 of Misra which are on siliciding zones above the source and drain regions, by the metal contact layer 15 of Ismail because in Ismail siliciding is not needed.

Claim 2

Layer 17 is not a second metal layer, but a dielectric layer (see column 5, line 26 and figures 9 and 9E).

Ismail does not teach or suggest to deposit two metal layers, the superficial metal layer having a greater mechanical resistance to polishing than the first metal layer.